

## IN THE SPECIFICATION

Please amend the paragraph at page 6, line 27 – page 7, line 12 as follows:

Terminal region 52 helps increase  $L_{eff}$  by concentrating the electric field lines to near the source and drain, away from much of the channel. In MOSFET 50, electric field lines between the n+ source S1 and substrate 54 are directed toward a section of p++ terminal region 52 near source S1. In FIG. 4, an electric field line E is shown much nearer the source/body boundary than in prior art FIG. 3. Likewise, electric field lines between the n+ drain D1 and substrate 54 are directed toward a section of p++ terminal region 52 near drain D1. Referring to FIG. [[5]] 7, section 70 72 is an example of a section that most of the electric field lines from source S1 would hit. Section 72 74 is an example of a section that most of the electric field lines from the drain (D D1) would hit. Sections 70 and 72 72 and 74 are shown in dashed lines because they do not necessarily include a different material than the remainder of terminal region 52. The precise locations of sections 70 and 72 72 and 74 depend on various factors including the depth of the source and drain, width between the source and drain, and the doping level of terminal region 52. In effect, terminal region 52 concentrates the electrical field lines in sections of terminal region 52 near the source and drain, dramatically reducing the amount of electrical field lines that cover channel 62. This results in a greater  $L_{eff}$  than would be occur without terminal region 52. Note that it is possible that some of the electric field lines may be through terminal region 52.